

Is Now Part of



ON Semiconductor®

To learn more about ON Semiconductor, please visit our website at www.onsemi.com

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any EDA Class 3 medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, emplo



November 2007

FDC365P

P-Channel PowerTrench[®] MOSFET -35V, -4.3A, $55m\Omega$

Features

- Max $r_{DS(on)} = 55m\Omega$ at $V_{GS} = -10V$, $I_D = -4.2A$
- Max $r_{DS(on)} = 80 \text{m}\Omega$ at $V_{GS} = -4.5 \text{V}$, $I_D = -3.2 \text{A}$
- RoHS Compliant

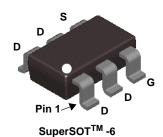
General Description

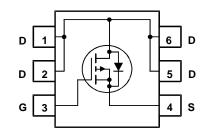
This P-Channel MOSFET has been produced using Fairchild Semiconductor's proprietary PowerTrench technology to deliver low $r_{DS(on)}$ and optimized Bvdss capability to offer superior performance benefit in the applications.

Applications

- Inverter
- Power Supplies







MOSFET Maximum Ratings $T_C = 25$ °C unless otherwise noted

Symbol	Parameter		Ratings	Units	
V _{DS}	Drain to Source Voltage		-35	V	
V_{GS}	Gate to Source Voltage		±20	V	
	-Continuous	(Note 1a)	-4.3	A	
ID.	-Pulsed		-20		
D	Power Dissipation	(Note 1a)	1.6	W	
P_{D}	Power Dissipation	(Note 1b)	0.8	VV	
T _J , T _{STG}	Operating and Storage Junction Temperature Range		-55 to +150	°C	

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1a)	78	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1b)	156	C/VV

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
.365P	FDC365P	SSOT6	7"	8mm	3000 units

Electrical Characteristics $T_J = 25$ °C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Chara	acteristics					
BV _{DSS}	Drain to Source Breakdown Voltage	$I_D = -250 \mu A, V_{GS} = 0 V$	-35			V
$\frac{\Delta BV_{DSS}}{\Delta T_{J}}$	Breakdown Voltage Temperature Coefficient	I_D = -250 μ A, referenced to 25°C		-26		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -28V, V_{GS} = 0V$			-1	μΑ
I _{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 20V, V_{DS} = 0V$			±100	nA

On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = -250 \mu A$	-1	-1.8	-3	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I _D = -250μA, referenced to 25°C		5.0		mV/°C
		$V_{GS} = -10V, I_D = -4.2A$		45	55	
r _{DS(on)}	r _{DS(on)} Static Drain to Source On Resistance	$V_{GS} = -4.5V, I_D = -3.2A$		70	80	mΩ
		$V_{GS} = -10V, I_D = -4.2A, T_J = 125$ °C		69	90	
9 _{FS}	Forward Transconductance	$V_{DS} = -10V, I_{D} = -4.2A$		8.7		S

Dynamic Characteristics

C _{iss}	Input Capacitance	V 20V V 0V	530	705	pF
C _{oss}	Output Capacitance	$V_{DS} = -20V, V_{GS} = 0V,$ f = 1MHz	105	135	pF
C _{rss}	Reverse Transfer Capacitance	1 - 1101112	55	80	pF
R_a	Gate Resistance	f = 1MHz	6.1		Ω

Switching Characteristics

t _{d(on)}	Turn-On Delay Time			7	13	ns
t _r	Rise Time	$V_{DD} = -20V, I_{D} = -4.2A,$ $V_{GS} = -10V, R_{GEN} = 6\Omega$		3	10	ns
t _{d(off)}	Turn-Off Delay Time	V _{GS} = -10V, K _{GEN} = 612		15	28	ns
t _f	Fall Time			3	10	ns
Q_{g}	Total Gate Charge	V _{GS} = 0V to -10V		11	15	nC
Q_{g}	Total Gate Charge	$V_{GS} = 0V \text{ to -5V}$ $V_{DD} = -20V_{DD}$,	6	9	nC
Q _{gs}	Gate to Source Charge	I _D = -4.2A		1.7		nC
Q_{gd}	Gate to Drain "Miller" Charge			2.2		nC

Drain-Source Diode Characteristics

V_{SD}	Source to Drain Diode Forward Voltage	$V_{GS} = 0V, I_{S} = -1.3A$ (Note 2)		-0.8	-1.2	V
t _{rr}	Reverse Recovery Time	L = 4.24 di/dt = 1004/vs		16	29	ns
Q _{rr}	Reverse Recovery Charge	I _F = -4.2A, di/dt = 100A/μs		7	14	nC

Notes:

Rouse. Is Rouse, is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Rouc is guaranteed by design while Rouse is determined by the user's board design.



a.78°C/W when mounted on a 1 in² pad of 2 oz copper on FR-4 board.



b.156°C/W when mounted on a minimum pad of 2 oz copper.

^{2:} Pulse Test: Pulse Width < $300\mu s$, Duty cycle < 2.0%.

Typical Characteristics T_J = 25°C unless otherwise noted

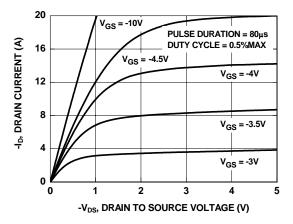


Figure 1. On-Region Characteristics

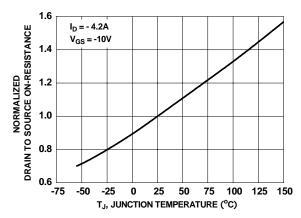


Figure 3. Normalized On-Resistance vs Junction Temperature

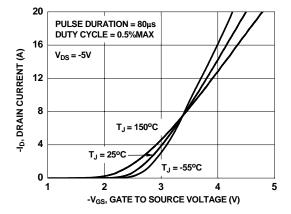


Figure 5. Transfer Characteristics

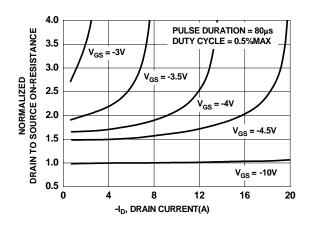


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

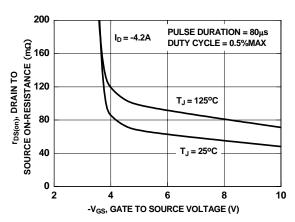


Figure 4. On-Resistance vs Gate to Source Voltage

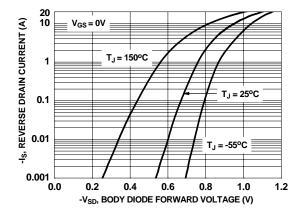


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics T_J = 25°C unless otherwise noted

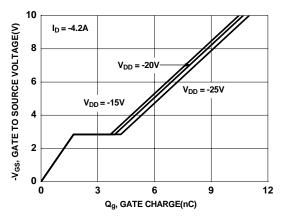


Figure 7. Gate Charge Characteristics

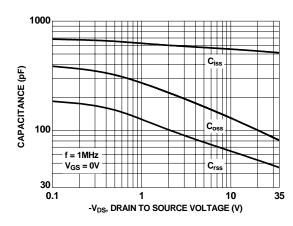


Figure 8. Capacitance vs Drain to Source Voltage

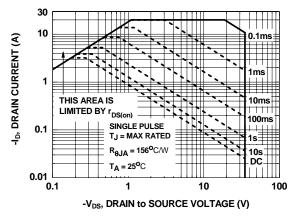


Figure 9. Forward Bias Safe Operating Area

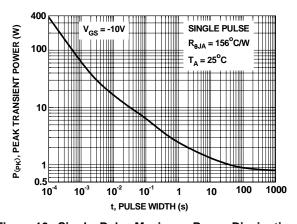


Figure 10. Single Pulse Maximum Power Dissipation

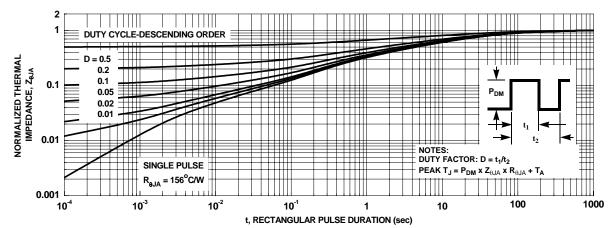
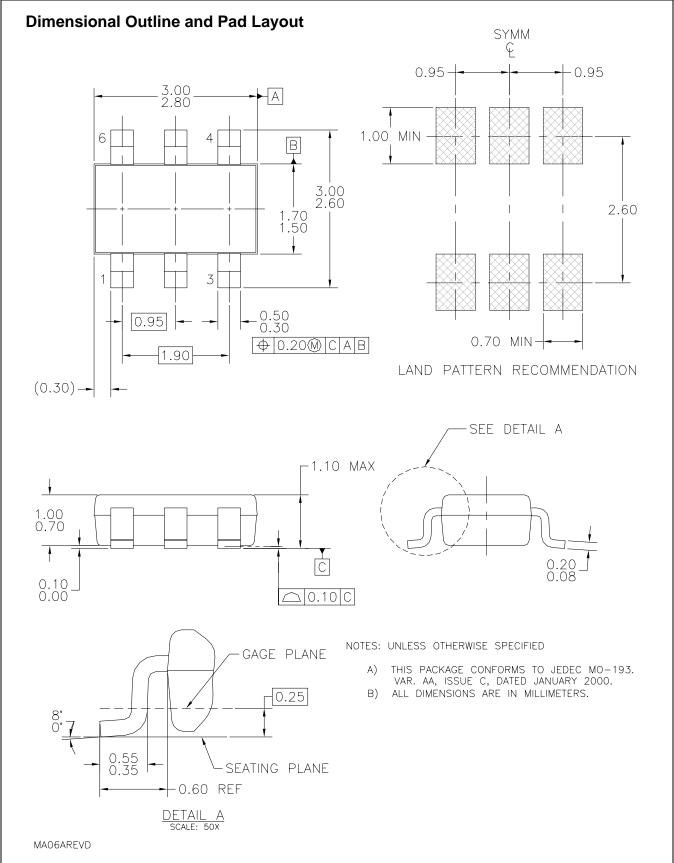


Figure 11. Transient Thermal Response Curve



Preliminary Datasheet



TRADEMARKS

The following are registered and unregistered trademarks and service marks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

ACFx® Green FPS™ Power247® SuperSOT™-8 Green FPS™ e-Series™ POWEREDGE[®] Build it Now™ SvncFET™ The Power Franchise® CorePLUS™ GTO™ Power-SPM™ i-Lo™ PowerTrench® $CROSSVOLT^{TM}$ Jwer' $\mathsf{CTL^{\mathsf{TM}}}$ Programmable Active Droop™ IntelliMAX™ ISOPLANAR™ **OFFT®** TinvBoost™ Current Transfer Logic™ EcoSPARK® TinyBuck™ MegaBuck™ QSTM TinyLogic[®] MICROCOUPLER™ QT Optoelectronics™ Fairchild[®] TINYOPTO™ MicroFET™ Quiet Series™ MicroPak™ RapidConfigure™ TinyPower™ Fairchild Semiconductor® TinyPWM™ FACT Quiet Series™ MillerDrive™ SMART START™ **FACT®** Motion-SPM™ SPM[®] TinyWire™ $\mathsf{FAST}^{\mathbb{B}}$ OPTOLOGIC® STEALTH™ µSerDes™ OPTOPLANAR® UHC® FastvCore™ SuperFET™ FPS™ UniFET™ SuperSOT™-3 FRFET® PDP-SPM™ SuperSOT™-6 VCX™ Power220® Global Power ResourceSM

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used herein:

- Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury to the user.
- A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information Formative or In Design		This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary First Production		This datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild Semiconductor. The datasheet is printed for reference information only.

ON Semiconductor and in are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdt/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and exp

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81–3–5817–1050

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative